**Product data sheet** 

## 1. Product profile

### 1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

### 1.2 Features and benefits

- Internally matched to 50  $\Omega$
- A gain of 26 dB at 950 MHz
- Output power at 1 dB gain compression = 1 dBm
- Supply current = 12.5 mA at a supply voltage of 3.3 V
- Reverse isolation > 36 dB up to 2 GHz
- Good linearity with low second order and third order products
- Noise figure = 4.1 dB at 950 MHz
- Unconditionally stable (K > 1)
- No output inductor required

### 1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

# 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	V <sub>CC</sub>		
2, 5	GND2		
3	RF_OUT		6—
4	GND1		4 2,5
6	RF_IN	<u> </u>	ילו לו
			sym052



### **MMIC** wideband amplifier

# 3. Ordering information

Table 2. Ordering information

Type number	Package	Package						
	Name	Description	Version					
BGA2802	-	plastic surface-mounted package; 6 leads	SOT363					

# 4. Marking

Table 3. Marking

Type number	Marking code	Description	
BGA2802	MA*		
		* = p : made in Hong Kong	
		* = W : made in China	
		* = t : made in Malaysia	

# 5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage	RF input AC coupled	-0.5	+5.0	V
I <sub>CC</sub>	supply current		-	55	mA
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 90 °C	-	200	mW
T <sub>stg</sub>	storage temperature		-40	+125	°C
Tj	junction temperature		-	125	°C
P <sub>drive</sub>	drive power		-	+10	dBm

### 6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$P_{tot} = 200 \text{ mW}; T_{sp} = 90 ^{\circ}\text{C}$	300	K/W

### 7. Characteristics

#### Table 6. Characteristics

 $V_{CC} = 3.3 \text{ V}; Z_S = Z_L = 50 \Omega; P_i = -40 \text{ dBm}; T_{amb} = 25 \text{ °C};$  measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		3.0	3.3	3.6	V
I <sub>CC</sub>	supply current		9.8	12.5	15.2	mA

BGA2802

## **MMIC** wideband amplifier

 Table 6.
 Characteristics ...continued

 $V_{CC} = 3.3 \ V; Z_S = Z_L = 50 \ \Omega; P_i = -40 \ dBm; T_{amb} = 25 \ ^{\circ}C;$  measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 250 MHz	25.0	25.6	26.2	dB
		f = 950 MHz	25.2	26	26.7	dB
		f = 2150 MHz	23.7	25.1	26.6	dB
RLin	input return loss	f = 250 MHz	12	14	16	dB
$\begin{array}{c} G_p & \text{power gain} \\ & f = 250 \text{ MHz} \\ & f = 950 \text{ MHz} \\ & f = 2150 \text{ MHz} \end{array}$		f = 950 MHz	14	17	19	dB
	16	22	29	dB		
RL <sub>out</sub>	output return loss	f = 250 MHz	19	23	27	dB
		f = 950 MHz	15	16	17	dB
		f = 2150 MHz	11	14	17	dB
ISL	isolation	f = 250 MHz	43	64	84	dB
		f = 950 MHz	47	49	51	dB
		f = 2150 MHz	36	40	42	dB
NF	noise figure	f = 250 MHz	3.7	4.2	4.7	dB
		f = 950 MHz	3.7	4.1	4.5	dB
		f = 2150 MHz	3.1	3.6	4.0	dB
B <sub>-3dB</sub>	-3 dB bandwidth	3 dB below gain at 1 GHz	2.5	2.7	2.9	GHz
	Rollett stability factor	f = 250 MHz	25	40	56	
		f = 950 MHz	5	6.5	7.5	
		f = 2150 MHz	1.5	2.5	3	
P <sub>L(sat)</sub>	saturated output power	f = 250 MHz	4	5	5	dBm
_(=,		f = 950 MHz	2	4	5	dBm
		f = 2150 MHz	-2	-1	0	dBm
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 250 MHz	2	3	3	dBm
_(:=-/		f = 950 MHz	0	1	3	dBm
		f = 2150 MHz	-4	-3	-2	dBm
IP3 <sub>I</sub>	input third-order intercept point	$P_{drive} = -40 \text{ dBm (for each tone)}$				
			-12	-10	-8	dBm
		- ·	-15	-13	-11	dBm
			-22	-19	26.6 16 19 29 27 17 17 84 51 42 4.7 4.5 4.0 2.9 56 7.5 3 5 0 3 3 -2	dBm
IP3 <sub>O</sub>	output third-order intercept point					
Ü			13	15	17	dBm
			11	13	15	dBm
			3	6	9	dBm
Pi (2H)	second harmonic output power					+
-(1)	- 41 11		-58	-56	-54	dBm
		f <sub>1H</sub> = 950 MHz; f <sub>2H</sub> = 1900 MHz	-48	-46		dBm
ΔIM2	second-order intermodulation distance	$P_{drive} = -40 \text{ dBm (for each tone)}$				
<b>-</b>		f <sub>1</sub> = 250 MHz; f <sub>2</sub> = 251 MHz	45	47	49	dBc
		$f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$	38	40		dBc

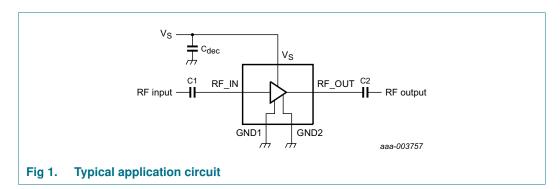
**MMIC** wideband amplifier

# 8. Application information

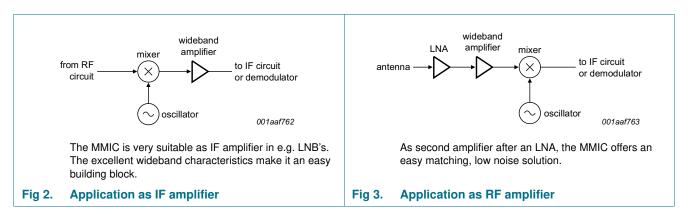
<u>Figure 1</u> shows a typical application circuit for the BGA2802 MMIC. The device is internally matched to  $50~\Omega$ , and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The location of the 470 pF supply decoupling capacitor ( $C_{dec}$ ) can be precisely chosen for optimum performance.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.

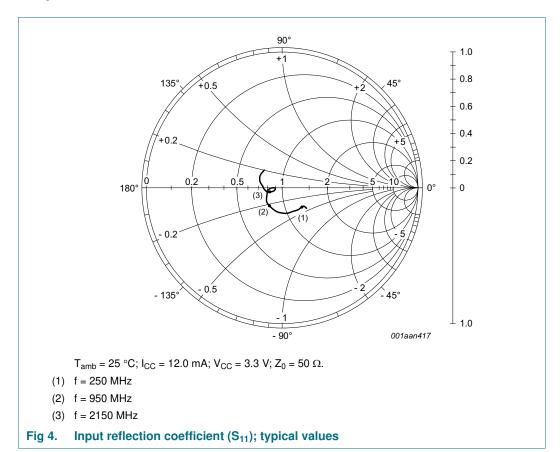


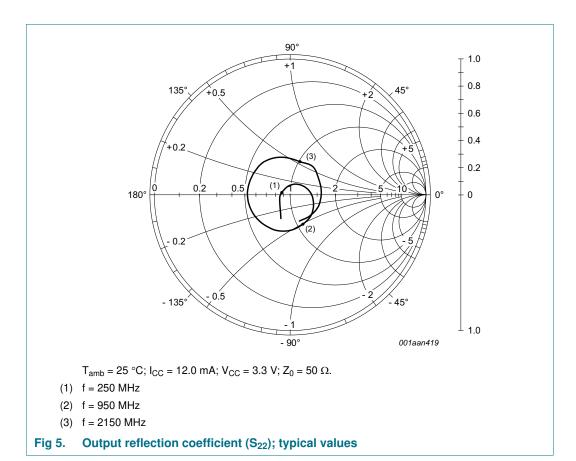
### 8.1 Application examples



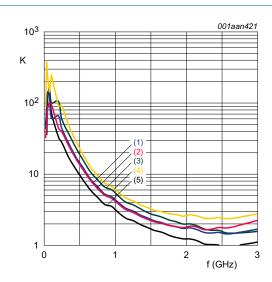
## **MMIC** wideband amplifier

# 8.2 Graphs





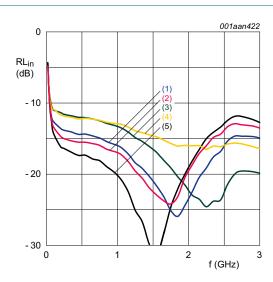
#### **MMIC** wideband amplifier



 $P_{drive} = -40 \text{ dBm}$ ;  $Z_0 = 50 \Omega$ .

- (1)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 10.00 \,\text{mA}$
- (2)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 11.10 \,\text{mA}$
- (3)  $V_{CC} = 3.3 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.00 \,\text{mA}$
- (4)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.90 \,\text{mA}$
- (5)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 14.20 \, \text{mA}$

Fig 6. Rollett stability factor as function of frequency; typical values

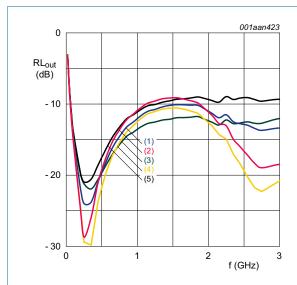


 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$ 

- (1)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 10.00 \,\text{mA}$
- (2)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 11.10 \,\text{mA}$
- (3)  $V_{CC} = 3.3 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.00 \,\text{mA}$
- (4)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.90 \,\text{mA}$
- (5)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 14.20 \,\text{mA}$

Fig 7. Input return loss as function of frequency; typical values

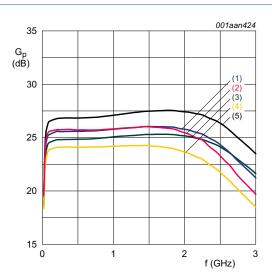
#### **MMIC** wideband amplifier



 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$ 

- (1)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 10.00 \,\text{mA}$
- (2)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 11.10 \,\text{mA}$
- (3)  $V_{CC} = 3.3 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.00 \,\text{mA}$
- (4)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.90 \,\text{mA}$
- (5)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 14.20 \,\text{mA}$

Fig 8. Output return loss as function of frequency; typical values

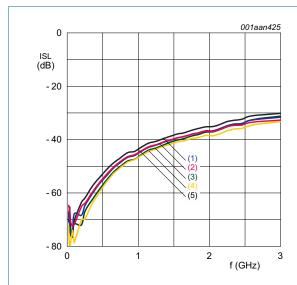


 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$ 

- (1)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 10.00 \,\text{mA}$
- (2)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 11.10 \, \text{mA}$
- (3)  $V_{CC} = 3.3 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.00 \,\text{mA}$
- (4)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.90 \,\text{mA}$
- (5)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 14.20 \,\text{mA}$

Fig 9. Power gain as function of frequency; typical values

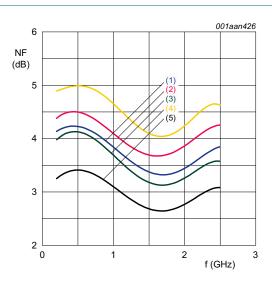
#### **MMIC** wideband amplifier



 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$ 

- (1)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 10.00 \,\text{mA}$
- (2)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 11.10 \,\text{mA}$
- (3)  $V_{CC} = 3.3 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.00 \,\text{mA}$
- (4)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.90 \,\text{mA}$
- (5)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 14.20 \,\text{mA}$

Fig 10. Isolation as function of frequency; typical values



 $Z_0 = 50 \Omega$ .

- (1)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 10.00 \,\text{mA}$
- (2)  $V_{CC} = 3.0 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 11.10 \,\text{mA}$
- (3)  $V_{CC} = 3.3 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.00 \,\text{mA}$
- (4)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 12.90 \,\text{mA}$
- (5)  $V_{CC} = 3.6 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 14.20 \,\text{mA}$

Fig 11. Noise figure as function of frequency; typical values

#### 8.3 Tables

**Table 7.** Supply current over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub> (°C)			Unit	
			-40	+25	+85		
I <sub>CC</sub>	supply current	$V_{CC} = 3.0 \text{ V}$	11.10	10.50	10.00	mA	
		$V_{CC} = 3.3 \text{ V}$	12.70	12.00	11.50	mA	
		$V_{CC} = 3.6 \text{ V}$	14.20	13.50	12.90	mA	

Table 8. Second harmonic output power over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	T <sub>amb</sub> (°C)		Unit	
			-40	+25	+85	
P <sub>L(2H)</sub>	second harmonic output power	$f = 250 \text{ MHz}$ ; $P_{drive} = -40 \text{ dBm}$				
		V <sub>CC</sub> = 3.0 V	-52	-55	-59	dBm
		V <sub>CC</sub> = 3.3 V	-53	-56	-59	dBm
		V <sub>CC</sub> = 3.6 V	-54	-56	-59	dBm
		$f = 950 \text{ MHz}$ ; $P_{drive} = -40 \text{ dBm}$				
		V <sub>CC</sub> = 3.0 V	-46	-47	-48	dBm
		V <sub>CC</sub> = 3.3 V	-45	-46	-48	dBm
		V <sub>CC</sub> = 3.6 V	-45	-46	-47	dBm

BGA2802

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Table 9. Input power at 1 dB gain compression over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub>	T <sub>amb</sub> (°C)			
			-40	+25	+85		
P <sub>i(1dB)</sub>	input power at 1 dB gain compression	f = 250 MHz					
		V <sub>CC</sub> = 3.0 V	-23	-23	-23	dBm	
		V <sub>CC</sub> = 3.3 V	-22	-22	-22	dBm	
		V <sub>CC</sub> = 3.6 V	-21	-22	-22	dBm	
		f = 950 MHz					
		V <sub>CC</sub> = 3.0 V	-23	-24	-24	dBm	
		V <sub>CC</sub> = 3.3 V	-23	-23	-24	dBm	
		V <sub>CC</sub> = 3.6 V	-22	-23	-24	dBm	
		f = 2150 MHz					
		$V_{CC} = 3.0 \text{ V}$	-26	-27	-28	dBm	
		V <sub>CC</sub> = 3.3 V	-26	-27	-29	dBm	
		V <sub>CC</sub> = 3.6 V	-26	-28	-29	dBm	

Table 10. Output power at 1 dB gain compression over temperature and supply voltages *Typical values.* 

Symbol	Parameter	Conditions	T <sub>amb</sub> (°C)		Unit	
			-40	+25	+85	
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 250 MHz				
		V <sub>CC</sub> = 3.0 V	1	1	1	dBm
		V <sub>CC</sub> = 3.3 V	3	3	2	dBm
		V <sub>CC</sub> = 3.6 V	4	4	3	dBm
		f = 950 MHz				
		V <sub>CC</sub> = 3.0 V	+1	0	-1	dBm
		V <sub>CC</sub> = 3.3 V	2	1	0	dBm
		V <sub>CC</sub> = 3.6 V	3	2	1	dBm
		f = 2150 MHz				
		V <sub>CC</sub> = 3.0 V	-2	-3	-6	dBm
		V <sub>CC</sub> = 3.3 V	-1	-3	-5	dBm
		V <sub>CC</sub> = 3.6 V	0	-2	-5	dBm

**Table 11.** Saturated output power over temperature and supply voltages *Typical values.* 

Symbol	Parameter	Conditions	T <sub>amb</sub>	(°C)		Unit
			-40	+25	+85	
P <sub>L(sat)</sub>	saturated output power	f = 250 MHz				
		V <sub>CC</sub> = 3.0 V	3	3	3	dBm
		$V_{CC} = 3.3 \text{ V}$	5	5	4	dBm
		V <sub>CC</sub> = 3.6 V	7	6	5	dBm
		f = 950 MHz				
		V <sub>CC</sub> = 3.0 V	3	2	2	dBm
		$V_{CC} = 3.3 \text{ V}$	4	4	3	dBm
		$V_{CC} = 3.6 \text{ V}$	6	5	3	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 \text{ V}$	0	-2	-4	dBm
		V <sub>CC</sub> = 3.3 V	+1	-1	-3	dBm
		V <sub>CC</sub> = 3.6 V	+1	-1	-3	dBm

Table 12. Second-order intermodulation distance over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub> (°C)			Unit
			-40	+25	+85	
ΔΙΜ2		$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		V <sub>CC</sub> = 3.0 V	36	42	56	dBc
		V <sub>CC</sub> = 3.3 V	40	47	67	dBc
		V <sub>CC</sub> = 3.6 V	44	51	63	dBc
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		V <sub>CC</sub> = 3.0 V	34	37	39	dBc
		V <sub>CC</sub> = 3.3 V	37	40	42	dBc
		V <sub>CC</sub> = 3.6 V	40	42	44	dBc

**Table 13.** Output third-order intercept point over temperature and supply voltages *Typical values.* 

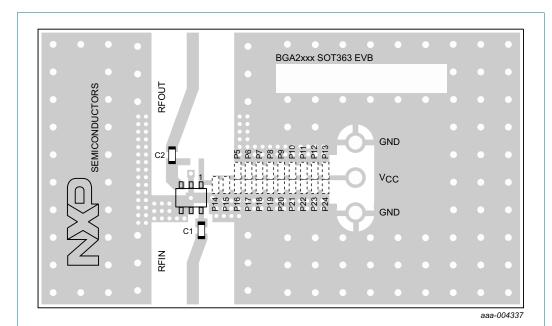
Symbol	Parameter	Conditions	T <sub>amb</sub>	T <sub>amb</sub> (°C)		
			-40	+25	+85	
IP3 <sub>O</sub>	output third-order intercept point	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	14	13	12	dBm
		V <sub>CC</sub> = 3.3 V	16	15	14	dBm
		V <sub>CC</sub> = 3.6 V	18	17	15	dBm
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 3.0 \text{ V}$	13	11	10	dBm
		$V_{CC} = 3.3 \text{ V}$	14	13	11	dBm
		V <sub>CC</sub> = 3.6 V	16	14	12	dBm
		$f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		V <sub>CC</sub> = 3.0 V	8	6	3	dBm
		V <sub>CC</sub> = 3.3 V	9	6	4	dBm
		V <sub>CC</sub> = 3.6 V	9	6	4	dBm

Table 14. -3 dB bandwidth over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub> (°C)			Unit
			-40	+25	+85	
B <sub>-3dB</sub>	-3 dB bandwidth	$V_{CC} = 3.0 \text{ V}$	2.922	2.768	2.595	GHz
		$V_{CC} = 3.3 \text{ V}$	2.912	2.756	2.584	GHz
		V <sub>CC</sub> = 3.6 V	2.902	2.743	2.568	GHz

**MMIC** wideband amplifier

## 9. Test information



For decoupling a decoupling capacitor ( $C_{dec}$ ) is used on one of the positions of P5 to P24. The results mentioned in this data sheet have been obtained using the decoupling capacitor  $C_{dec}$  on position P22. The distance between the center of pin 1 and the center of position P22 is 7.43 mm.

Fig 12. PCB layout and demo board with components

Table 15. List of components used for the typical application

Component	Description	Value	Dimensions	Remarks
C1, C2	multilayer ceramic chip capacitor	470 pF	0603	X7R RF coupling capacitor
P5 to P24 [1]	position for multilayer ceramic chip capacitor C <sub>dec</sub>	470 pF	0603	X7R RF decoupling capacitor
IC1	BGA2802 MMIC	-	SOT363	

[1] For decoupling a decoupling capacitor (C<sub>dec</sub>) is used on one of the positions of P5 to P24. The results mentioned in this data sheet have been obtained using the decoupling capacitor C<sub>dec</sub> on position P22.

# 10. Package outline

### Plastic surface-mounted package; 6 leads

**SOT363** 

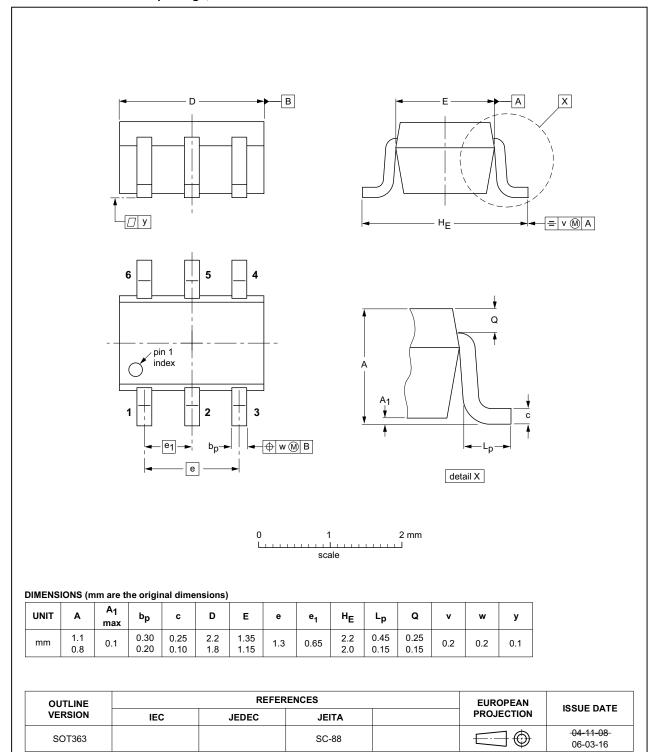


Fig 13. Package outline SOT363

RGA2802

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### **MMIC** wideband amplifier

# 11. Abbreviations

Table 16. Abbreviations

Acronym	Description
IF	Intermediate Frequency
LNA	Low-Noise Amplifier
LNB	Low-Noise Block converter
PCB	Printed-Circuit Board
SMD	Surface Mounted Device

# 12. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGA2802 v.6	20150713	Product data sheet	-	BGA2802 v.5	
Modifications:	The format of to of NXP Semice		sheet has been redesigned to comply with the new identity guidelines rs.		
	<ul> <li>Legal texts have</li> </ul>	ve been adapted to the new c	ompany name where a	appropriate.	
BGA2802 v.5	20141209	Product data sheet	-	BGA2802 v.4	
BGA2802 v.4	20130823	Product data sheet	-	BGA2802 v.3	
BGA2802 v.3	20121010	Product data sheet	-	BGA2802 v.2	
BGA2802 v.2	20110415	Product data sheet	-	BGA2802 v.1	
BGA2802 v.1	20110224	Product data sheet	-	-	

#### **MMIC** wideband amplifier

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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#### **MMIC** wideband amplifier

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### **MMIC** wideband amplifier

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